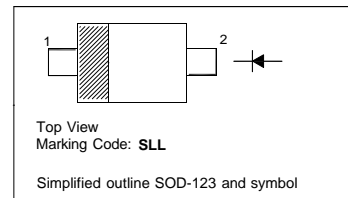


0.8A Surface Mount Schottky Barrier Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	40	V
Average Forward Rectified Current	$I_{F(AV)}$	0.8	A
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine-Wave)	I_{FSM}	6	A
Power Dissipation	P_{tot}	450	mW
Operating Temperature Range	T_j	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1\text{ mA}$	$V_{(BR)R}$	40	-	V
Reverse Current at $V_R = 40\text{ V}$ at $V_R = 4\text{ V}$ at $V_R = 6\text{ V}$	I_R	- - -	1 0.05 0.075	mA
Forward Voltage at $I_F = 0.1\text{ A}$ at $I_F = 0.8\text{ A}$	V_F	- -	0.45 0.62	V
Total Capacitance at $V_R = 4\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	120	pF

Typical Characteristics

1N5819WL

